



UNITED STATES DEPARTMENT OF COMMERCE
Patent and Trademark Office
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APPLICATION NUMBER	FILING DATE	FIRST NAMED APPLICANT	ATTORNEY DOCKET NO.
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10/046,346

EXAMINER

G. Munson

ART UNIT	PAPER NUMBER
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14

DATE MAILED:

INTERVIEW SUMMARY

All participants (applicant, applicant's representative, PTO personnel):

(1) B. Johnson (3) _____

(2) _____ (4) _____

Date of interview 2 March 2004

Type: Telephonic Televideo Conference Personal (copy is given to applicant applicant's representative).

Exhibit shown or demonstration conducted: Yes No If yes, brief description: _____

Agreement was reached. was not reached.

Claim(s) discussed: 1,7

Identification of prior art discussed: Suzuki, Edmond et al, Hermansson

Description of the general nature of what was agreed to if an agreement was reached, or any other comments: Discussed case and possible distinctions over the references.

(A fuller description, if necessary, and a copy of the amendments, if available, which the examiner agreed would render the claims allowable must be attached. Also, where no copy of the amendments which would render the claims allowable is available, a summary thereof must be attached.)

It is not necessary for applicant to provide a separate record of the substance of the interview.

Unless the paragraph above has been checked to indicate to the contrary. A FORMAL WRITTEN REPLY TO THE LAST OFFICE ACTION IS NOT WAIVED AND MUST INCLUDE THE SUBSTANCE OF THE INTERVIEW. (See MPEP Section 713.04). If a reply to the last Office action has already been filed, APPLICANT IS GIVEN ONE MONTH FROM THIS INTERVIEW DATE TO FILE A STATEMENT OF THE SUBSTANCE OF THE INTERVIEW.

Examiner Note: You must sign this form unless it is an attachment to another form.

Gene M. Munson
GENE M. MUNSON
EXAMINER
GROUP ART UNIT 2831

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Serial No. 10/046,346

Proposed Claim:

A bipolar structure comprising:

a silicon carbide substrate;

an n⁺ type epitaxially grown terminating layer on said substrate;

an n⁻ type voltage blocking region of silicon carbide on said n⁺ type terminating layer;

a p-type epitaxially grown terminating layer **on said blocking region**

wherein said n⁺ and p type terminating layers each have a respective **thickness greater than the minority carrier diffusion length** in said layers.